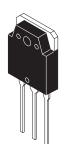
### **WPB4001**

## **N-Channel Power MOSFET** 500V, 26A, 0.26Ω, TO-3P-3L

# ON

#### ON Semiconductor®

http://onsemi.com



TO-3P-3L

#### **Features**

- ON-resistance RDS(on)= $0.2\Omega$  (typ.)
- Input capacitance Ciss=2250pF (typ.)
- 10V Drive

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		500	V
Gate to Source Voltage	VGSS		±30	V
Drain Current (DC)	ID		26	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	90	Α
Source to Drain Diode Forward Current (DC)	ISD		26	А
Source to Drain Diode Forward Current (Pulse)	ISDP	PW≤10μs, duty cycle≤1%	90	А
Allowable Power Dissipation	PD		2.5	W
		Tc=25°C	220	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		543	mJ
Avalanche Current *2	IAV		14	А

Note: \*1 VDD=50V, L=5mH, IAV=14A (Fig.1)

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

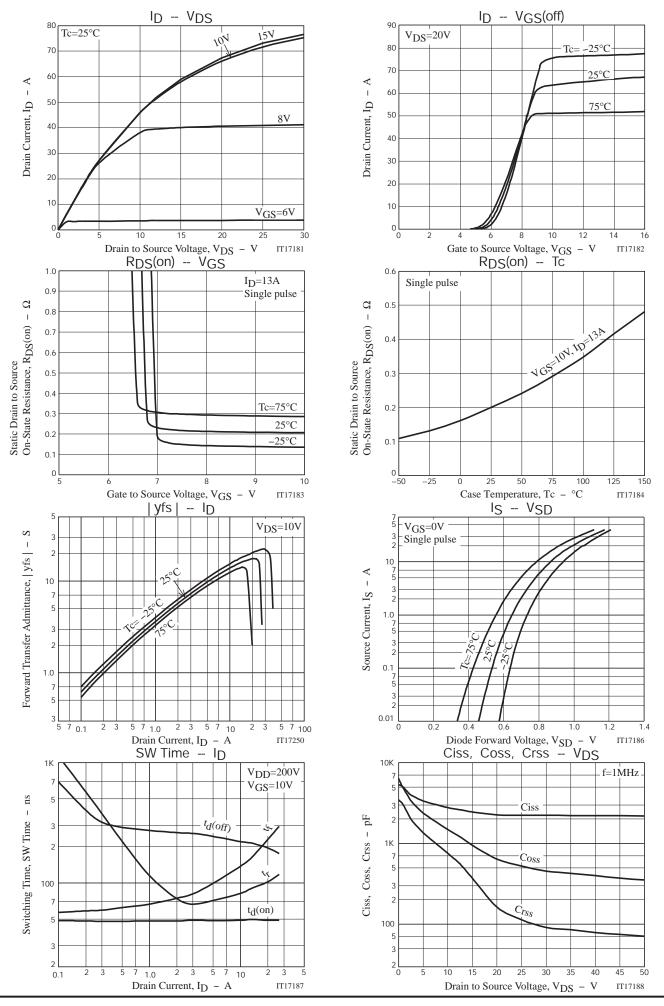
#### Electrical Characteristics at Ta=25°C

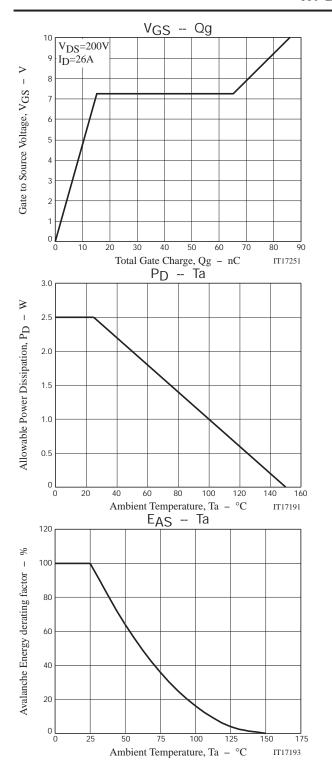
Parameter	Symbol	Conditions	Ratings			11.71
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =400V, V <sub>GS</sub> =0V			100	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V			±100	nA
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	3		5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =13A	7.5	15.5		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)	I <sub>D</sub> =13A, V <sub>G</sub> S=10V		0.20	0.26	Ω
Input Capacitance	Ciss			2250		pF
Output Capacitance	Coss	V <sub>DS</sub> =30V, f=1MHz		450		pF
Reverse Transfer Capacitance	Crss			90		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See Fig.2		44		ns
Rise Time	t <sub>r</sub>			156		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			224		ns
Fall Time	tf			94		ns
Total Gate Charge	Qg	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V, I <sub>D</sub> =26A		87		nC
Gate to Source Charge	Qgs			15.2		nC
Gate to Drain "Miller" Charge	Qgd			50		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =26A, V <sub>GS</sub> =0V		1.1	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	See Fig.3		115		ns
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>SD</sub> =26A, V <sub>GS</sub> =0V, di/dt=100A/μs		340		nC

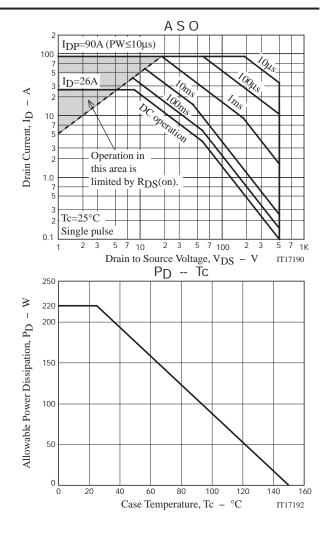
#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 4 of this data sheet.

<sup>\*2</sup> L≤5mH, single pulse







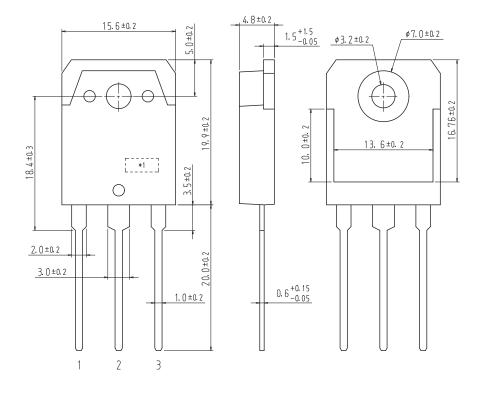
#### **Package Dimensions**

WPB4001-1E

TO-3P-3L CASE 340AF ISSUE O

Unit : mm

- 1: Gate
- 2: Drain
- 3: Source





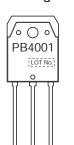
These dimension do not include mold protrusion

\*1:Lot indication

#### Ordering & Package Information

•	•		
Device	Package	Shipping	memo
WPB4001-1E	TO-3P-3L SC-65, SOT-199, TO-247	30 pcs./tube	Pb-Free

#### Marking



#### **Electrical Connection**

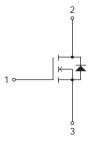
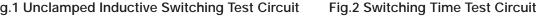
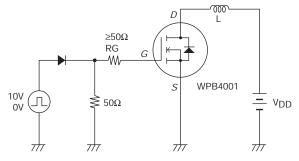


Fig.1 Unclamped Inductive Switching Test Circuit





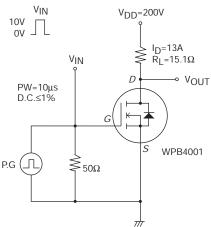
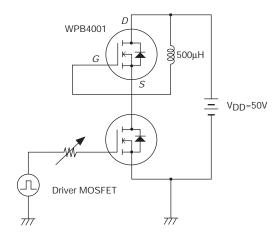


Fig.3 Reverse Recovery Resistance Test Circuit



Note on usage: Since the WPB4001 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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